

Best Student Award ⁱⁿ Electronic Devices

Presented to

Liubou Padzialiashkina

Processing and Characterization on N-polar GaN/AlGaN
Heterostructure Field-Effect Transistors Grown on 200mm
Sapphire Substrates



ICNS 15

Malmö, Sweden 2025

Åsa Haglund

Enik Lind

Guangxi Ju

Supported by

Applied Physics
Letters

Journal of
Applied Physics

AIP Advances